

**PHOTORESPONSE FROM FERROELECTRIC CAPACITORS:
OPTICAL PROBING/CONDITIONING OF FERROELECTRIC
THIN FILM MEMORIES**

JPL

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AUGUST 10, 1994

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5.22
**Presented at the International Symposium of Applied Ferroelectrics held
August 7-10, 1994 at Penn State Scanticon, State College, Pennsylvania**



OUTLINE

- WHAT IS PHOTORESPONSE?
 - A SENSITIVE PHENOMENON THAT REFLECTS THE
“STATE OF AFFAIRS” OF THE FERRO-FILM/CAPACITOR
- “ HOW DOES ONE MEASURE IT?
 - **USE OF ACCOUSTO-OPTICALLY SWITCHED PULSED LASER FOR NOISE REDUCTION**
- WHAT DOES ONE DO WITH IT?
 - PROBING AND CONDITIONING OF FATIGUED SAMPLES
“ PROBING FOR “HISTORY” OF THE SAMPLES
- “ CONCLUSIONS



INTRODUCTION

- KINDS OF PHOTO RESPONSE:
 - PHOTO INDUCED CURRENT/VOLTAGE
 - TRANSMITTED LIGHT
 - REFLECTED LIGHT

- INCIDENT LIGHT PARAMETERS
 - WAVELENGTH
 - INTENSITY
 - POLARIZATION
 - CONTINUOUS/PULSED
 - ANGLE OF INCIDENCE

NON-DESTRUCTIVE LASER PULSE PROBING JPL OF THE FERROELECTRIC CAPACITOR

SCHEMATIC OPTICAL SET-UP

ACOUSTO-OPTICALLY
SWITCHED

Nd-YAG
LASER
1.064 μm

DOUBLER

532 nm

ATTENUATOR

HALF- POLA-
WAVE RIZER
PLATE

BEAM
SPLITTER

ATTENUATING FILTER

PHOTODETECTOR

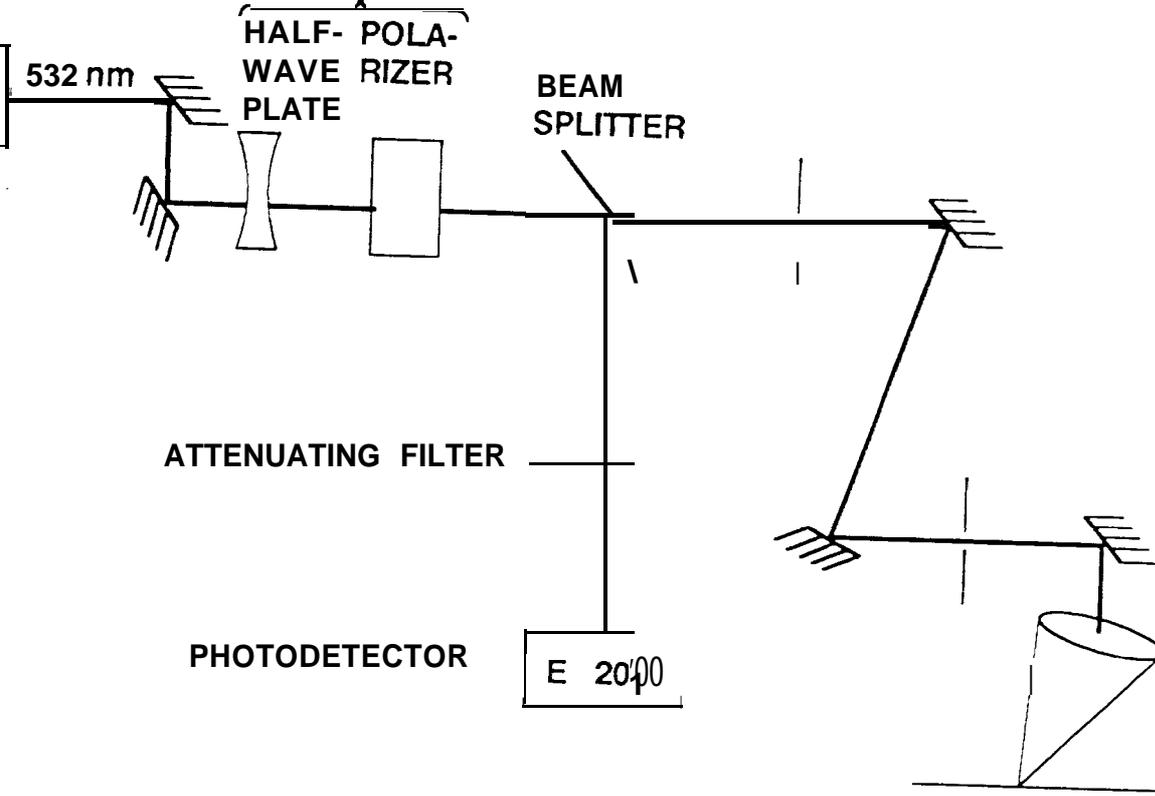
E 2040

BEAM
FOCUSING
LENS

DUT (Device Under
Test)
MOUNTED
ON PROBE
STATION

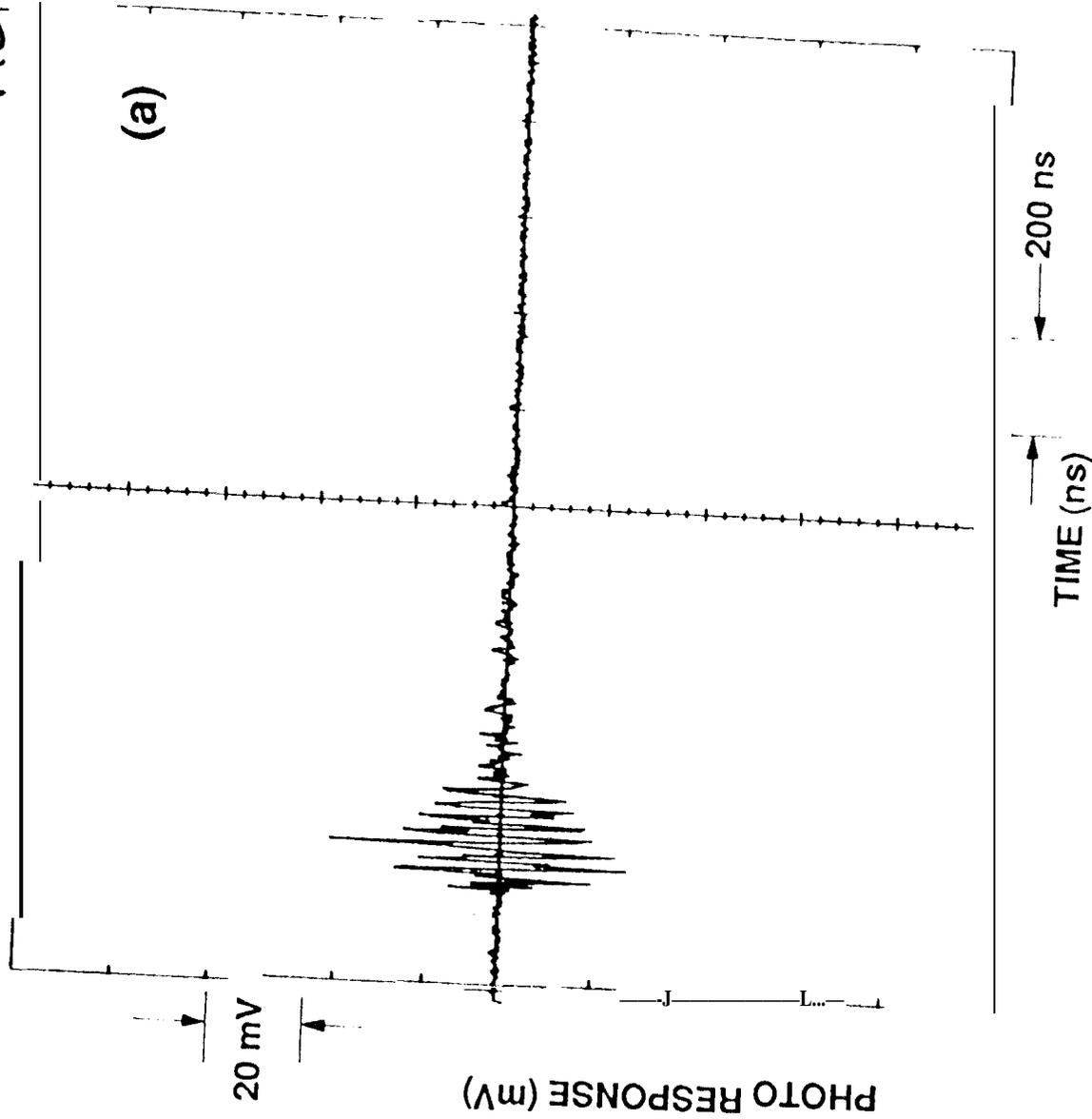
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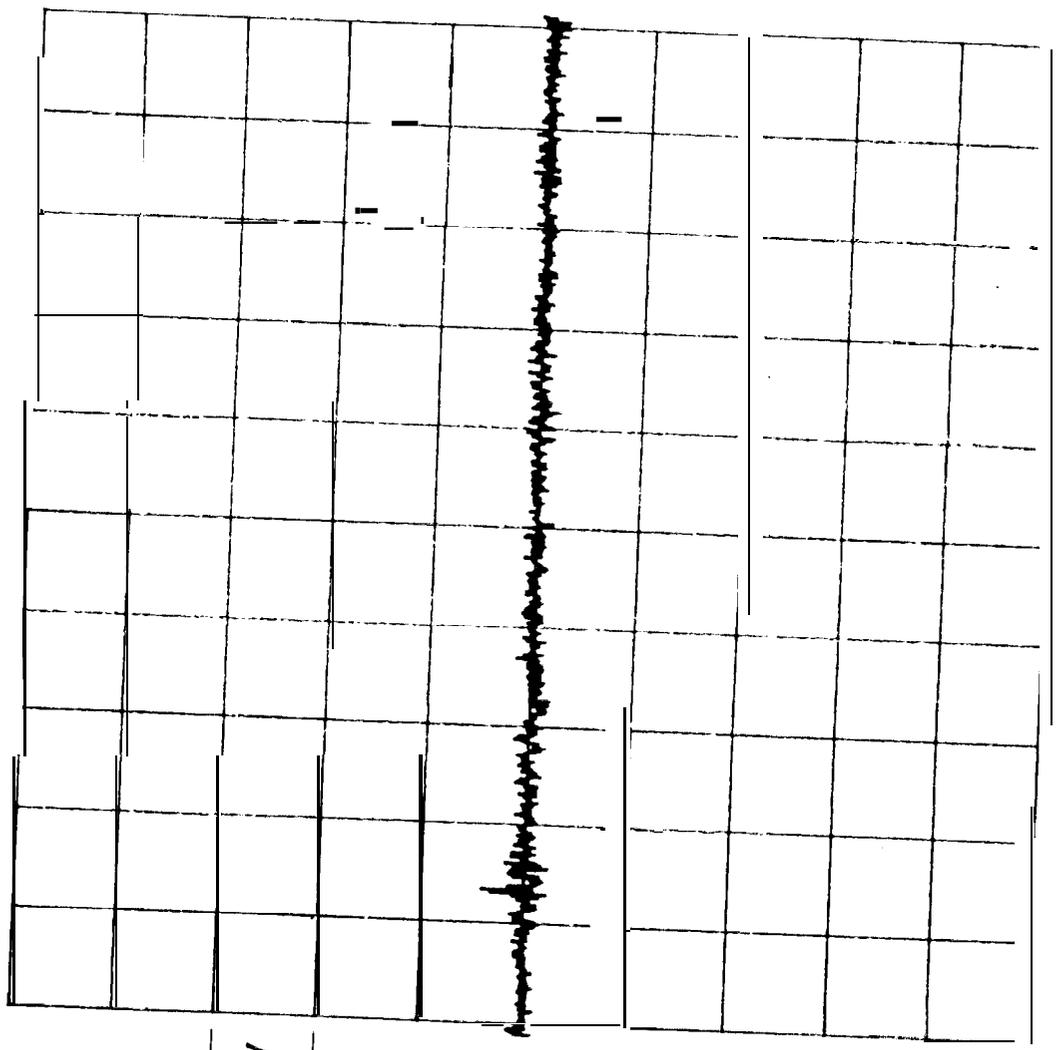


ELECTRO OPTICALLY SWITCHED
LASER (LARGE NOISE
PICK UP)



ACCOUSTO OPTICALLY SWITCHED LASER
LOW NOISE SIGNAL FOR HIGH SPEED
PHOTORESPONSE MEASUREMENT

→ PL



PHOTORESPONSE (mV)

TIME (ns)

200 ns



EXPERIMENTAL DETAILS

- TRANSMISSION RESPONSE 200 nm-800 nm USING CAREY MODEL 5A SPECTROPHOTOMETER
 - DC, MULTIMAGNETRON SPUTTERED PZT (S. THAKOOR, U.S. PATENT #5196101 (23 MARCH 1993))
ANGLE OF INCIDENCE OF SPUTTER DEPOSIT: CONTROL PARAMETER
FILM A: DEPOSITED USING ALL ANGLES OF DEPOSITION
FILM B: DEPOSITION ANGLE RESTRICTED TO PERPENDICULAR INCIDENCE
 - SURFACE TOPOGRAPHY INSPECTED USING CAMBRIDGE S250 SEM

- BANDGAP LIGHT ILLUMINATION:
 - SHORT ARC MERCURY LAMP: UV VISIBLE ILLUMINATION SOURCE (300-600 nm)
365 nm FILTER USED TO OBTAIN $\sim 100 \text{ mW/cm}^2$
ILLUMINATION PULSE LENGTH VARIABLE FROM 1-99 sec
HYSTERISIS LOOPS OBSERVED AS FUNCTION OF ILLUMINATION

- HIGH SPEED EFFECTS: 532 nm Nd.YAG PULSED LASER
 - PULSE WIDTH $\sim 10 \text{ ns}$, POWER $.6 \text{ mW}/\mu\text{m}^2$
PHOTORESPONSE MEASURED DIFFERENTIALLY ACROSS 50Ω INPUT IMPEDENCE OF A DSA 602A TEKTRONIX DIGITIZING SIGNAL ANALYZER



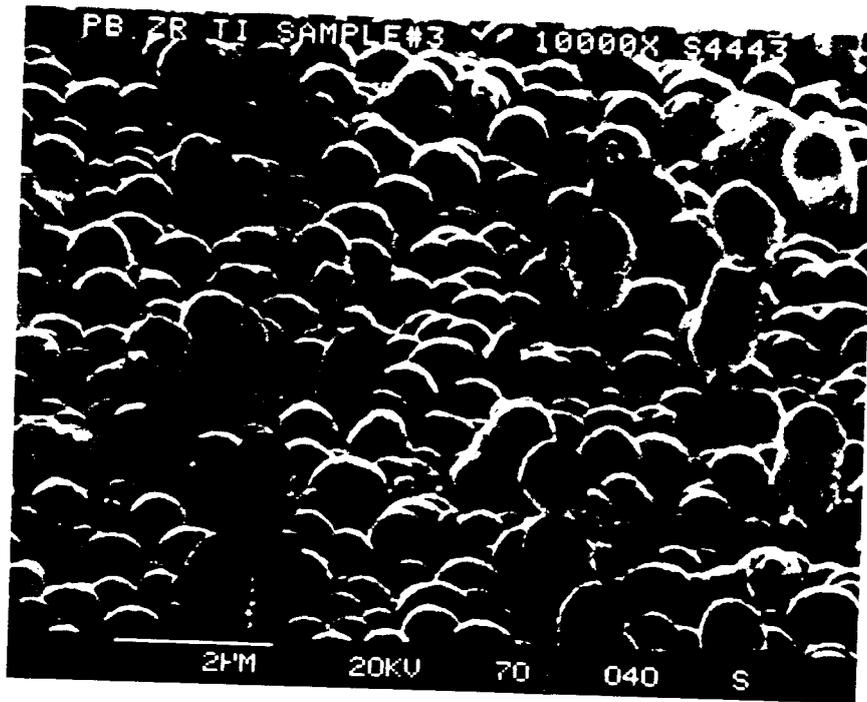
PZT FILMS SOL-GEL DEPOSITED FILMS*:

- **BASE ELECTRODE: Ti/Pt (1000&I 000 Å)**
- **PZT COMPOSITION (Zr:52, Ti:48)
18% EXCESS LEAD**
- **TOP ELECTRODE: DC SPUTTER-DEPOSITED
SEMITRANSSPARENT Pt (~150 Å)
OPTICAL TRANSMISSION ~30%**

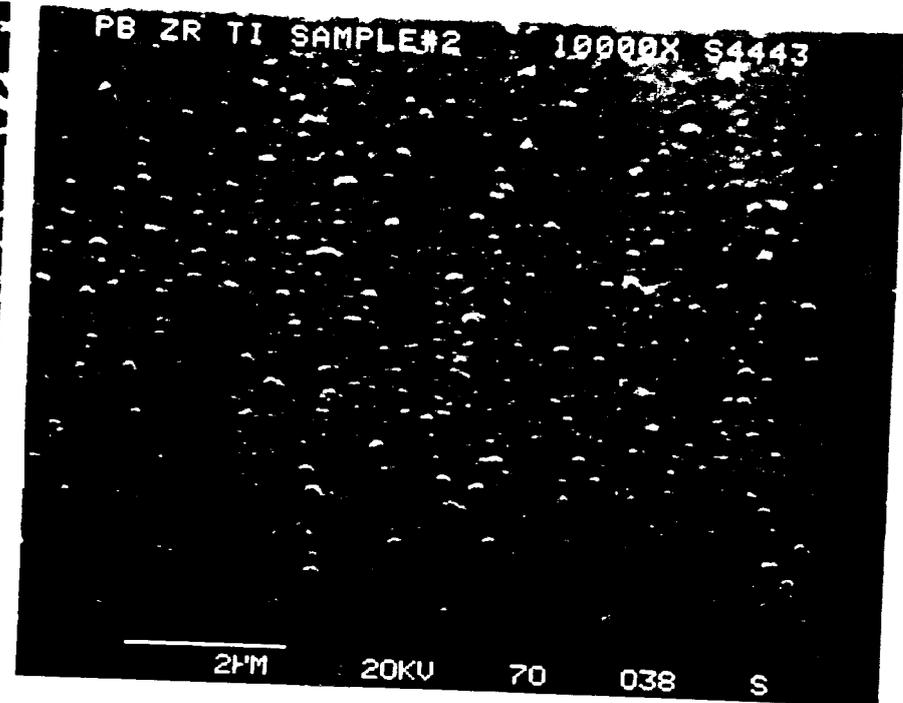
* 1. G. YI, Z. WU AND M. SAYER, JAP 64, 2717 (1988)
2. S.E. BERNSTEIN et al, FERROELECTRIC THIN FILMS II
MRS PROC. VOL. 243, P. 343

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SURFACE TOPOGRAPHY OF SEQUENTIAL, REACTIVE, MAGNETRON, SPUTTER DEPOSITED PZT



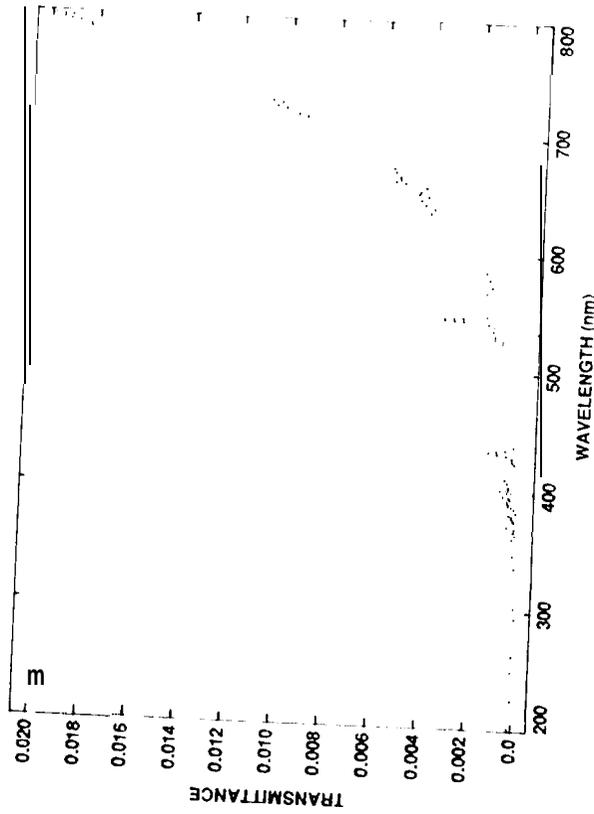
PZT: HIGH OPTICAL
SCATTERING
SURFACE ROUGHNESS $\sim 1\mu\text{m}$



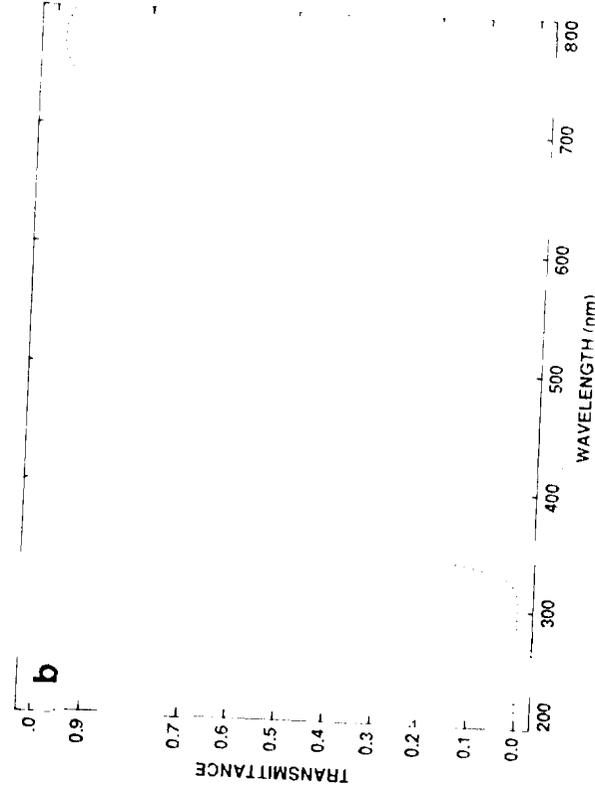
PZT: GOOD OPTICAL
TRANSMITTANCE
SURFACE ROUGHNESS $\sim 0.2\mu\text{m}$

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COMPARISON OF TRANSMISSION SPECTRA MULTIMAGNETRON DC SPUTTERED PZT



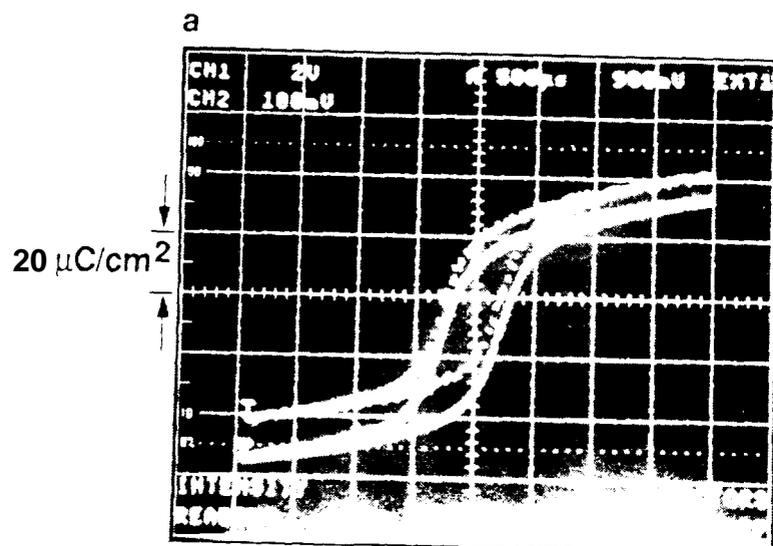
PZT: HIGH OPTICAL
SCATTERING
SURFACE ROUGHNESS $\sim 1\mu\text{m}$



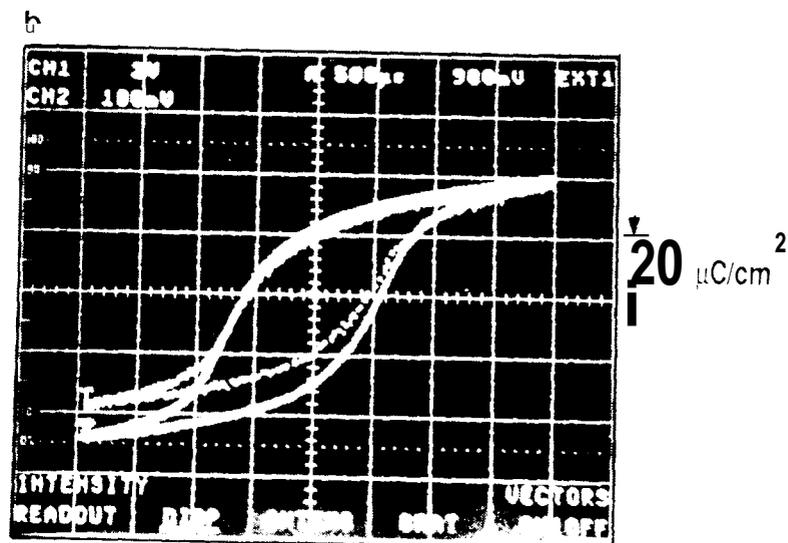
PZT: GOOD OPTICAL
TRANSMITTANCE
SURFACE ROUGHNESS $\sim 0.2\mu\text{m}$

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EFFECT OF BANDGAP ILLUMINATION COMPARISON UNFATIGUED AND FATIGUED STATE



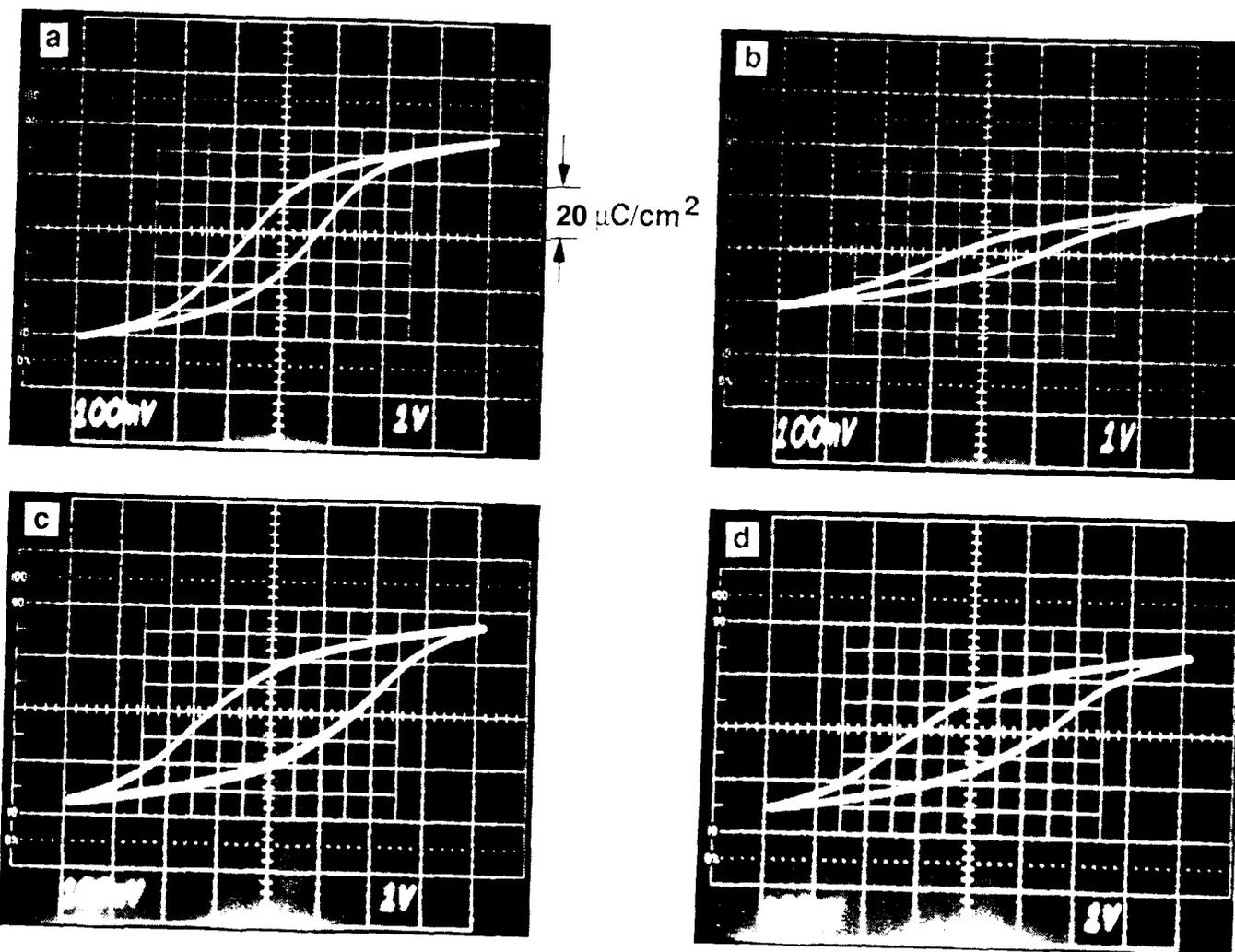
UNFATIGUED



FATIGUED, 10^8 CYCLES

DOTTED LINE - W; THOUT ILLUMINATION
FULL LINE - WITH ILLUMINATION

EFFECT OF BANDGAP ILLUMINATION ON FATIGUED CAPACITOR



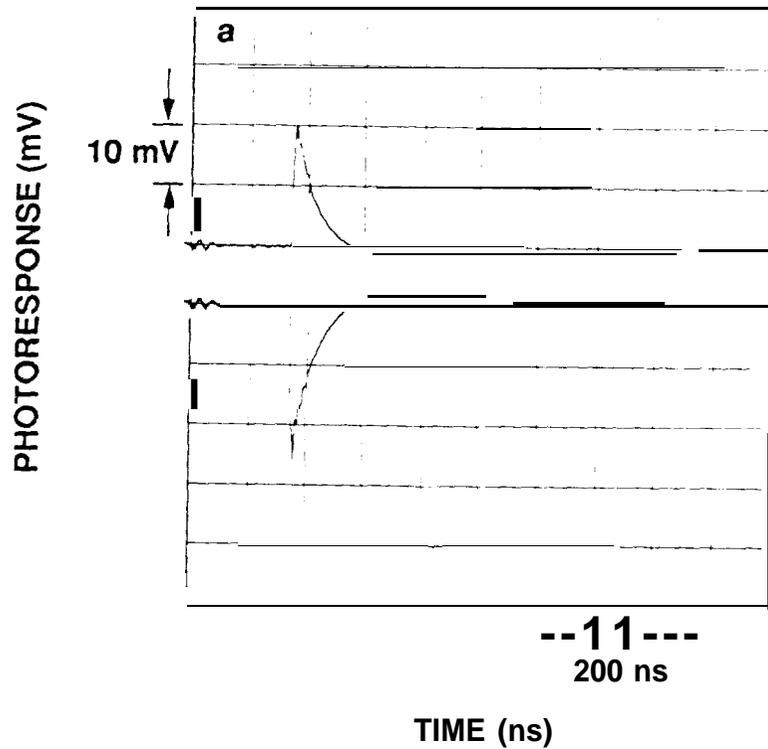
HYSTERESIS LOOPS AT 500 Hz: (a) : INITIAL STATE · (b) : FATIGUED STATE
 (c) : ILLUMINATION REJUVENATED STATE, 1st LOOP AFTER ILLUMINATION TURN-OFF
 (d) : ILLUMINATION OF REJUVENATED STATE, STEADY STATE LOOP AFTER ILLUMINATION TURN-OFF.



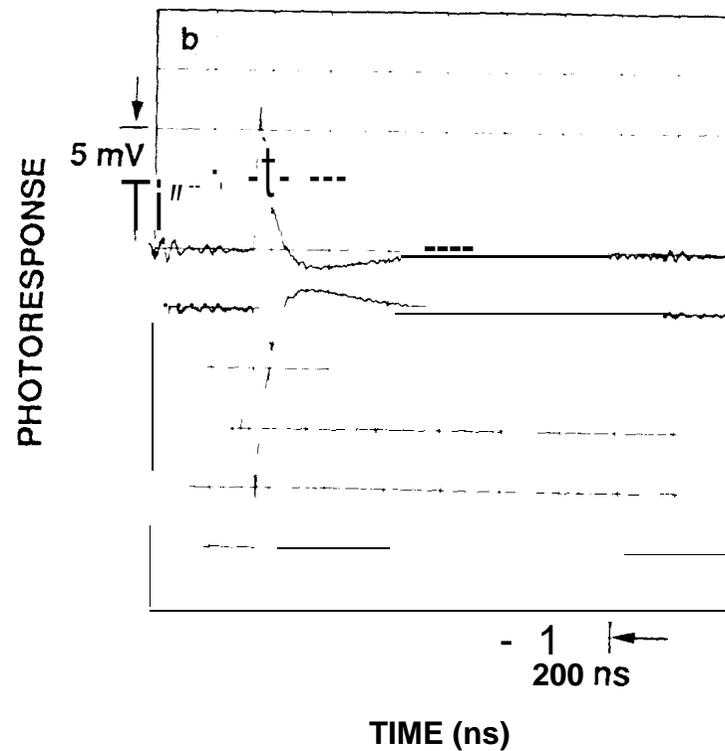
BANDGAP ILLUMINATION EFFECTS

- 365 nm ILLUMINATION CAUSES THE HYSTERESIS LOOP TO SHIFT AS WELL AS BLOOM
- **UNFATIGUED** CAPACITORS AND MILDLY FATIGUED CAPACITORS PRIMARILY SHOW ONLY A PHOTOINDUCED CONDUCTIVITY CHANGE AS INDICATED BY HYSTERESIS LOOP REVERTING BACK TO VIRTUALLY ORIGINAL STATE ON TURN-OFF OF ILLUMINATION
- FATIGUED SAMPLES ($\sim 10^{10}$ CYCLES) **CAN** BE CONDITIONED USING BANDGAP LIGHT
 - IMPROVED REMANENT POLARIZATION SUGGESTS DE-PINNING OF PINNED DOMAINS/REMOVAL OF SCREENING **FIELDS**
 - INCREASED COERCIVE VOLTAGE SUGGESTS INCREASE IN THE **NON-FERROELECTRIC** (RESISTIVE) INTERFACE/SURFACE LAYER IN THE **FERROELECTRIC DEVICE** STRUCTURE

**HIGH SPEED PHOTORESPONSE:
UNFATIGUED INITIAL STATE**

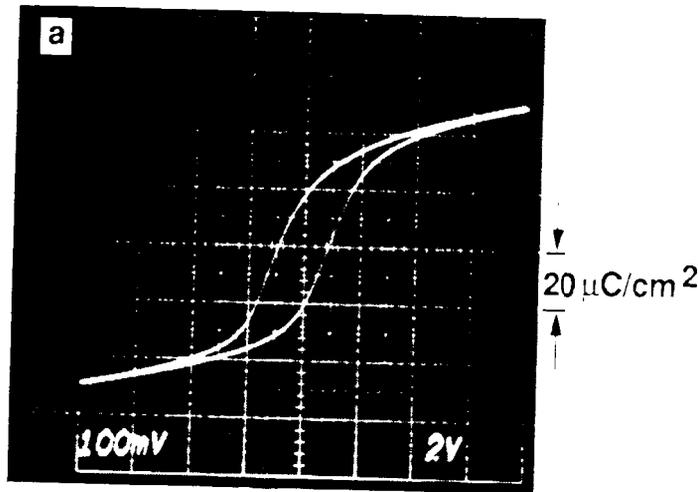


**HIGH SPEED PHOTORESPONSE:
FATIGUED STATE**

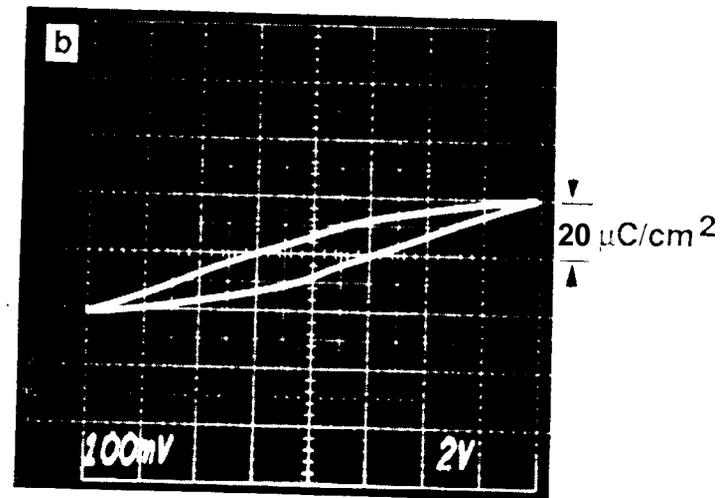


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HYSTERESIS LOOPS (1 kHz) FATIGUED AND UNFATIGUED STATES COMPARISON

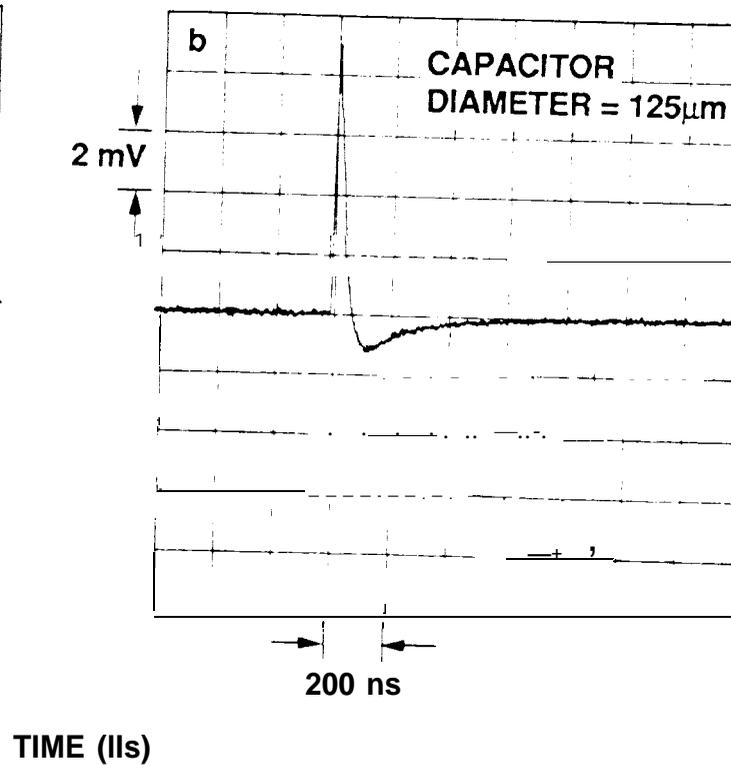
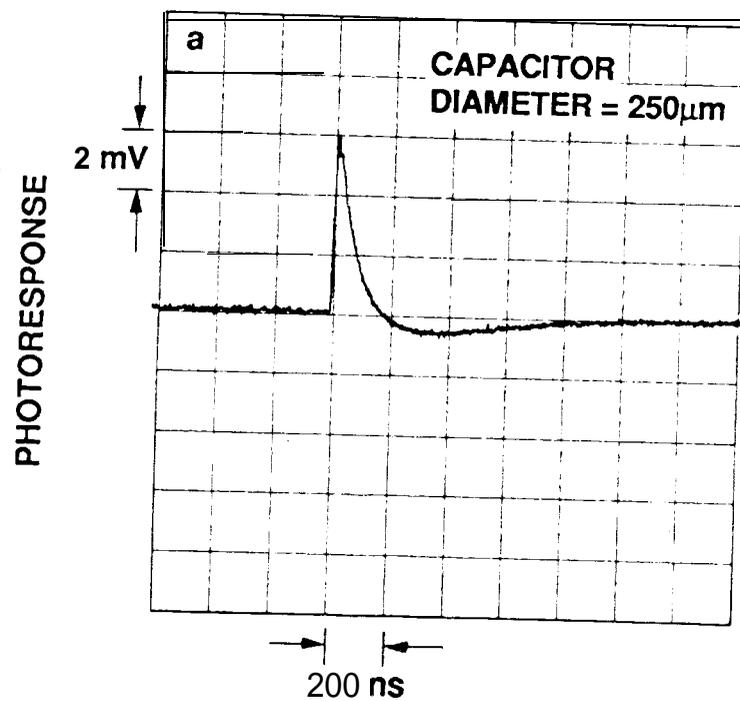


UNFATIGUED INITIAL STATE



FATIGUED STATE (10^{10} CYCLES)

HIGH SPEED PHOTORESPONSE: EFFECT OF CAPACITANCE.





High Speed Photoresponse Analysis

Poling Polarity	Ratio: $\frac{\text{Unfatigued Polarization}}{\text{Fatigued Polarization}}$ determined by hysteresis loop	Ratio: $\frac{\text{Area under peak, unfatigued}}{\text{Area under peak, fatigued}}$ determined by photoresponse
positive	2.57	2.57
negative	2.62	2.65



HIGH SPEED PHOTOEFFECT

“ **AREA** UNDER THE PHOTORESPONSE PEAK, A_R

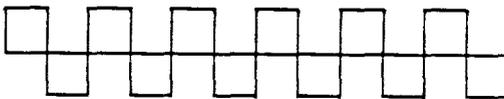
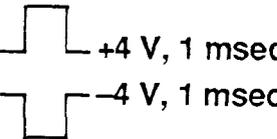
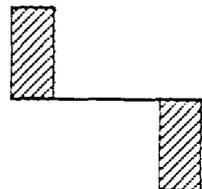
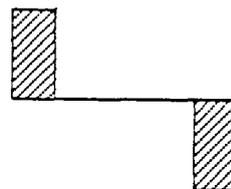
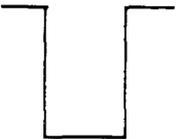
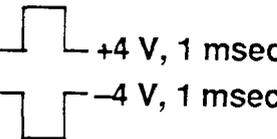
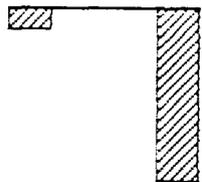
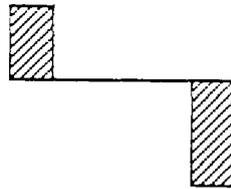
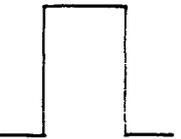
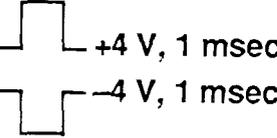
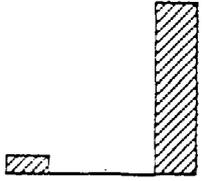
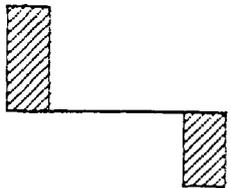
“ $A_R \propto \Delta P_R$, CHANGE OF POLARIZATION ASSOCIATED WITH INCIDENCE OF ILLUMINATION PULSE

- **ALSO**, $\Delta P_R \propto P_R$, POLARIZATION OF THE FERRO-CAPACITOR

SO $A_R \propto P_R$

- SPEED OF PHOTO RESPONSE \propto CAPACITANCE
- THE ILLUMINATION PULSE IS NON-INVASIVE .
THE CHANGE ΔP_R IS FOLLOWED BY AN EQUIVALENT $-\Delta P_R$
SO THERE IS NO NET CHANGE IN P_R AS VERIFIED
INDEPENDENTLY BY USING DRO WITH AND WITHOUT
ILLUMINATION

JPL PHOTORESPONSE: PROBING FOR "HISTORY" OF THE FERROELECTRIC CAPACITORS

HISTORY	READOUT		
	POLING	PHOTORESPONSE	DRO, POLARIZATION
 <p>± 4 V, 1 msec, BIPOLAR</p>	 <p>+4 V, 1 msec -4 V, 1 msec</p>		
 <p>-5 V, 10 sec</p>	 <p>+4 V, 1 msec -4 V, 1 msec</p>		
 <p>+5 V, 10 sec</p>	 <p>+4 V, 1 msec -4 V, 1 msec</p>		

CONCLUSIONS:**• HIGH SPEED PHOTOEFFECT**

- **AREA UNDER THE PHOTORESPONSE PEAK, (A_R), PROVIDES AN EXCELLENT NON-INVASIVE, QUANTITATIVE MEASURE OF REMANENT POLARIZATION (P_R)**
- **SPEED OF PHOTORESPONSE IS DIRECTLY DICTATED BY THE DEVICE CAPACITANCE, THEREFORE, WITH REDUCING FERROELECTRIC PIXEL SIZE, THE RESPONSE SPEED BECOMES PROPORTIONALLY FASTER**
- **HIGH SPEED PHOTOEFFECT REFLECTS SENSITIVELY THE POLARIZATION HISTORY OF THE FERROELECTRIC CAPACITOR**

• BANDGAP ILLUMINATION EFFECTS

- **FATIGUED SAMPLES CAN BE CONDITIONED USING BANDGAP LIGHT**
- **STEADY PHOTOCURRENT CAN SERVE AS INDICATOR OF CAPACITOR INTERFACE STATUS (S. Thakoor, JAP 75 (10), p. 5409, May 1994)**

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ACKNOWLEDGEMENTS

- DR. JANE ALEXANDER, ARPA
- DR. STEVE BERNACKI, RAYTHEON
- PROF. ERIC CROSS PENN STATE
- DR. P. LARSEN PHILLIPS, NETHERLANDS
- DR. R. RAMESH BELLCORE

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